PNP Silicon Epitaxial Planar Transistor

for audio power amplifier

The transistor is subdivided into two groups, O and Y, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.18g

Absolute Maximum Ratings (Ta=25°C)

	Symbol	Value	Unit
Collector to Base Voltage	-V _{CBO}	30	V
Collector to Emitter Voltage	-V _{CEO}	30	V
Emitter to Base Voltage	-V _{EBO}	5	V
Collector Current	-I _C	2	Α
Power Dissipation	P _{tot}	1	W
Operating and Storage Junction Temperature	T _j ,T _S	-55 to +150	°С







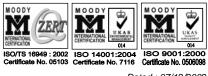
ST 2SA928

Characteristics at T_{amb}=25 °C

		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at - V_{CE} =2 V , - I_{C} =500 mA	Ο	h _{FE}	100	-	200	-
	Υ	h _{FE}	160	-	320	-
Collector Cutoff Current						
at -V _{CB} =30V		-I _{CBO}	-	-	0.1	μА
Emitter Cutoff Current						
at -V _{EB} =5V		-I _{EBO}	-	-	0.1	μΑ
Collector-Emitter Breakdown Voltage						
at -I _C =10mA		-V _{(BR)CEO}	30	-	-	V
Collector-Base Breakdown Voltage						
at - I_C =100 μ A		-V _{(BR)CBO}	30	-	-	V
Emitter-Base Breakdown Voltage						
at -I _E =1mA		-V _{(BR)EBO}	5	-	-	V
Output Capacitance						
at -V _{CB} =10V, f=1MHz		Cob	-	48	-	pF
Collector to Emitter Saturation Voltage						
at $-I_C=1.5A$, $-I_B=0.03A$		-V _{CE(sat)}	-	-	2	V
Base-Emitter Voltage						
at - V_{CE} =2 V , - I_{C} =500 mA		-V _{BE}	-	-	1	V
Transition Frequency						
at -V _{CE} =2V, -I _C =500mA		f _T	-	120	-	MHz









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